Rev.A Dec.-2023

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	30	V
Drain Current - Continuous		I_D	30	A
Drain Current – Pulsed		I_{DM}	140	A
Gate-Source Voltage		V_{GS}	± 20	V
Power Dissipation		$P_D(T_c=25\ \ )$	31	W
Single Pulse Avalanche Energy(L=0.1mH)		E_{AS}	50	mJ
Avalanche Current(L=0.1mH)		I_{AS}	22.5	A
Junction and Storage Temperature Range		T_j, T_{stg}	-55 to 150	
Thermal resistance, junction - ambient	t ≤ 10s	$R_{\theta JA}$	21	/ W
	Steady-State		53	

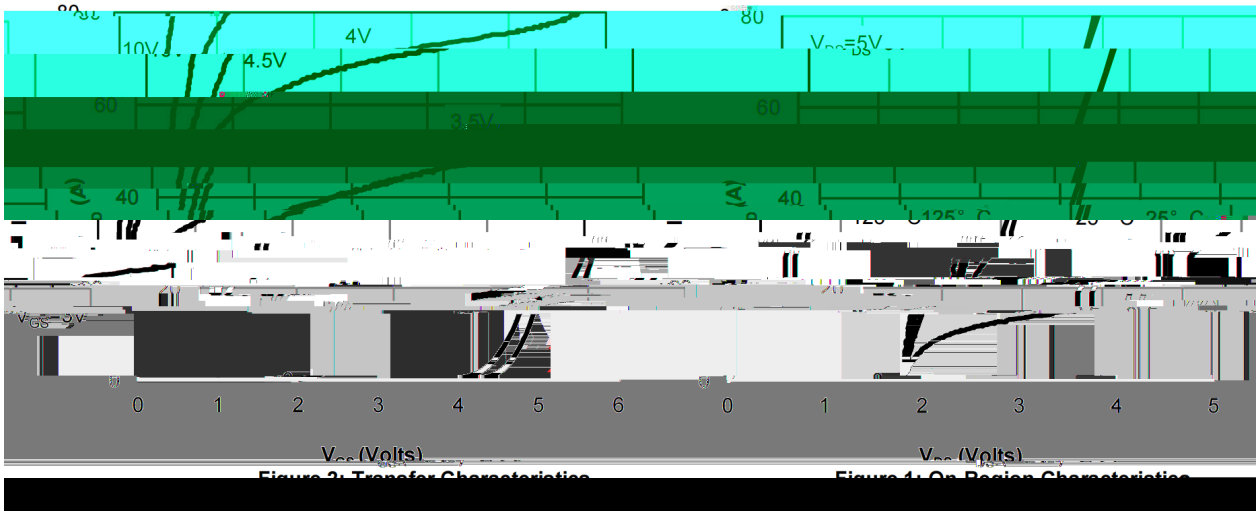

Figure 2: Transfer Characteristics

Figure 1: On-Region Characteristics

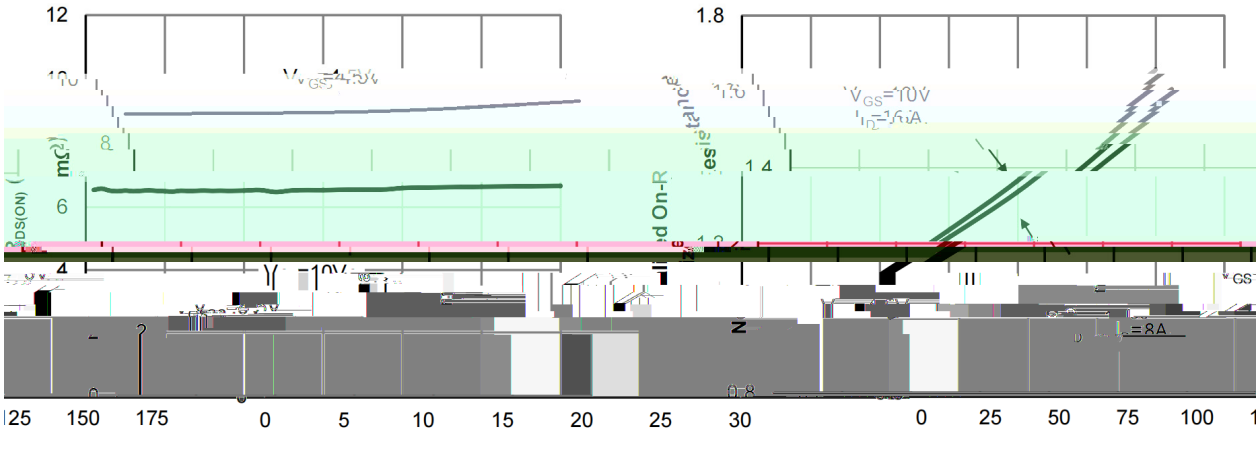

Figure 3: On-Resistance vs. Drain Current and Gate Voltage

Figure 4: On-Resistance vs. Drain Current and Gate Voltage

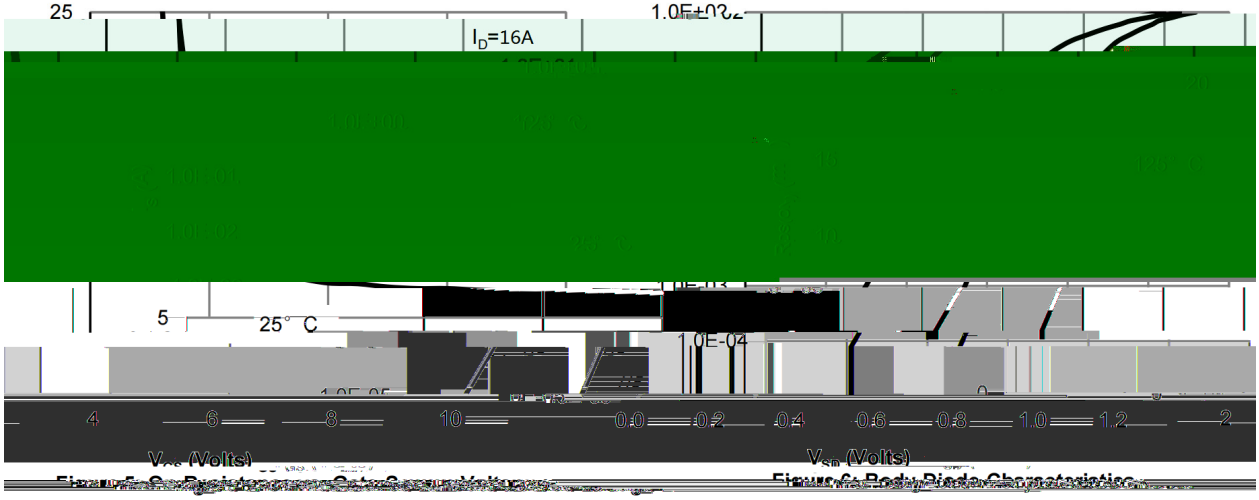

Figure 5: On-Resistance vs. Gate Source Voltage

Figure 6: Body Diode Characteristics

Note:

1	150 200 60 120sec;	1.Preheating:150~200	, Time:60~120sec.
2	255±5 5±0.5sec;	2.Peak Temp.:255±5	, Duration:5±0.5sec.
3	2 10 /sec.	3. Cooling Speed: 2~10	/sec.

260±5	10±1 sec.	Temp.:260±5	Time:10±1 sec

/ REEL